

The following replacement claims are respectfully submitted:

1. (Amended) A method for manufacturing a capacitor of a semiconductor

device, comprising:

forming a storage electrode over a semiconductor substrate;

forming a high dielectric layer over the storage electrode;

forming a plate electrode over the high dielectric layer;

a1  
performing a first post-annealing of the semiconductor substrate under an inert atmosphere at a first temperature; and

performing a second post-annealing of the semiconductor substrate, after the first post-annealing, at a second temperature lower than the first temperature,

the first and second post-annealings being performed in-situ.

9. (Amended) A method for manufacturing a capacitor of a semiconductor

device, comprising:

a2  
Cmt  
forming a storage electrode over a semiconductor substrate;

forming a high dielectric layer over the storage electrode;

forming a plate electrode over the high dielectric layer;

forming a  
B  
atmosphere; and

performing a second post-annealing of the semiconductor substrate, after the first post-annealing, at a second temperature lower than the first temperature,

*A<sup>2</sup>*  
*Canceled*  
the first and second post-annealings being performed after the forming of the  
plate electrode.

*A<sup>3</sup>*  
*Inventor*  
*C<sup>3</sup>*  
12. (Amended) A method for manufacturing a capacitor of a semiconductor device, comprising:

forming a storage electrode over a semiconductor substrate;  
forming a high dielectric layer over the storage electrode;  
forming a plate electrode over the high dielectric layer;  
performing a first post-annealing of the semiconductor substrate under an inert atmosphere at a first temperature;  
performing a second post-annealing of the semiconductor substrate, after the first post-annealing, at a second temperature lower than the first temperature; and  
forming an interdielectric layer over the plate electrode,  
the first and second post-annealings being performed after the forming of the interdielectric layer.

*A<sup>4</sup>*  
*Inventor*  
*C<sup>4</sup>*  
15. (Amended) A method for manufacturing a capacitor of a semiconductor device in which a storage electrode, a high dielectric layer, a plate electrode, and an interdielectric layer are sequentially formed on a semiconductor substrate, further comprising:

performing a first post-annealing of the semiconductor substrate under an inert

*Just  
C4  
off  
Cm id*

atmosphere at a first temperature; and

performing a second post-annealing of the semiconductor substrate, after the first post-annealing, at a second temperature lower than the first temperature, the first and second post-annealings being performed after forming of the plate electrode.